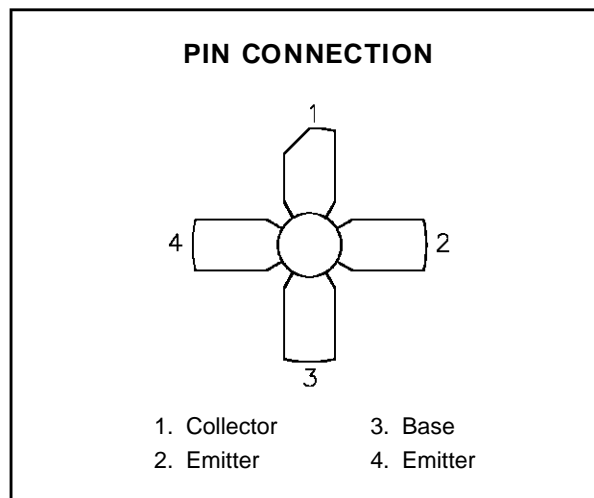
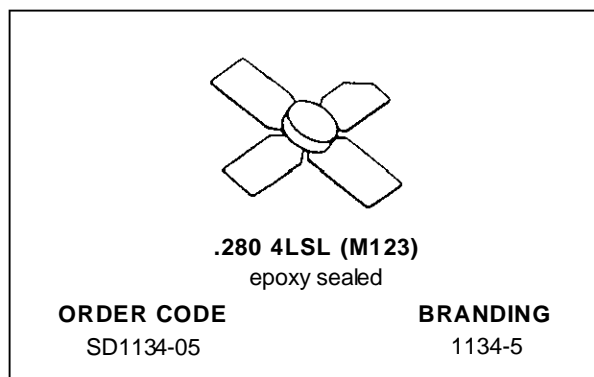


**RF & MICROWAVE TRANSISTORS
VHF PORTABLE/MOBILE APPLICATIONS**

- 175 MHz
- 7.5 VOLTS
- COMMON EMITTER
- P_{OUT} = 0.5 W MIN. WITH 7.0 dB GAIN


DESCRIPTION

The SD1134-05 is a 7.5 V epitaxial silicon NPN planar transistor designed primarily for VHF communications. It with stands very high VSWR under rated operating conditions.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	36	V
V _{CER}	Collector-Emitter Voltage	16	V
V _{CES}	Collector-Emitter Voltage	36	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _c	Device Current	0.75	A
P _{DISS}	Power Dissipation	5.0	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +150	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance	35	°C/W
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SD1134-05**ELECTRICAL SPECIFICATIONS** ($T_{\text{case}} = 25^{\circ}\text{C}$)

STATIC

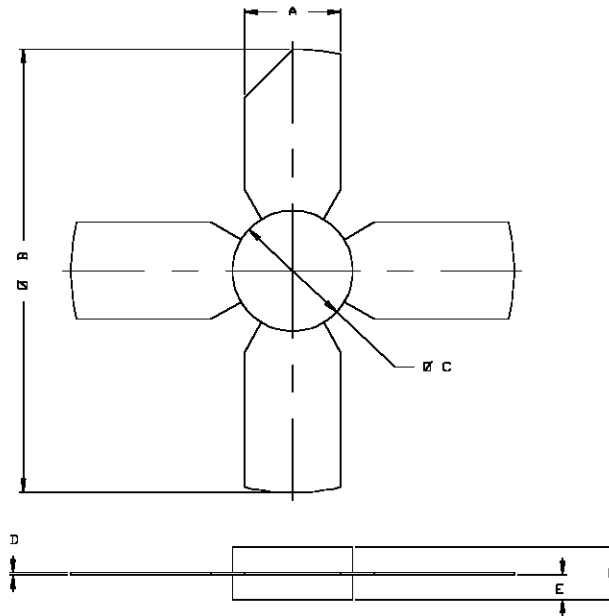
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CES}	$I_{\text{C}} = 5\text{mA}$	$V_{\text{BE}} = 0\text{V}$	36	—	—	V
BV_{CEO}	$I_{\text{C}} = 25\text{mA}$	$I_{\text{B}} = 0\text{mA}$	16	—	—	V
BV_{EBO}	$I_{\text{E}} = 1\text{mA}$	$I_{\text{C}} = 0\text{mA}$	4.0	—	—	V
I_{CER}	$V_{\text{CE}} = 10\text{V}$	$R_{\text{BE}} = 80\Omega$	—	—	0.5	mA
I_{CBO}	$V_{\text{CB}} = 15\text{V}$	$I_{\text{E}} = 0\text{mA}$	—	—	1.0	mA
h_{FE}	$V_{\text{CE}} = 5\text{V}$	$I_{\text{C}} = 100\text{mA}$	40	—	200	—

DYNAMIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
P_{OUT}	$f = 150\text{ MHz}$	$V_{\text{CC}} = 7.5\text{ V}$	1.4	—	—	W
G_{P}	$f = 150\text{ MHz}$	$V_{\text{CC}} = 7.5\text{ V}$	11.5	—	—	dB
C_{OB}	$f = 1\text{ MHz}$	$V_{\text{CB}} = 7.5\text{ V}$	—	6.0	—	pF

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0123



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	-----	1.055/26,8
C	.275/6,99	.285/7,24
D	.004/0,10	.006/0,15
E	.050/1,27	.060/1,52
F	.118/3,00	.130/3,30

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